

APPENDIX B - Unmarked Claims As Amended Or Newly Entered

1. A method for the preparation of a dispersion of zinc sulfide particles doped with copper (ZnS:Cu), said method comprising the step of performing a precipitation by mixing together a zinc salt, a sulfide, and a citrate or EDTA complex of copper ions, dissolved in several aqueous solutions.
2. A method according to claim 1 wherein said precipitation is performed according to the double jet principle, whereby a first solution containing said zinc salt and said citrate or EDTA complex of copper ions, and a second solution containing said sulfide are added simultaneously to a third solution.
3. A method according to claim 1 wherein said copper ions are copper (I) ions.
4. A method according to claim 3 wherein said copper (I) ions are incorporated as copper (I) chloride.
5. A method according to any of claim 1 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.
6. A method according to claim 5 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.

7. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 1.
8. A method according to claim 2 wherein said copper ions are copper (I) ions.
9. A method according to claim 8 wherein said copper (I) ions are incorporated as copper (I) chloride.
10. A method according to any of claim 2 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.
11. A method according to claim 10 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.
12. A method according to any of claim 3 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.
13. A method according to claim 12 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.
14. A method according to any of claim 4 further comprising the step of subjecting the mixture formed by said precipitation step to a diafiltration and/or ultrafiltration treatment.

15. A method according to claim 14 wherein said diafiltration and/or ultrafiltration treatment is performed in the presence of a compound preventing agglomeration of said ZnS:Cu particles.
16. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 2.
17. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 3.
18. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 4.
19. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 5.
20. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 6.
21. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 7.
22. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 8.

23. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 9.
24. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 10.
25. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 11.
26. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 12.
27. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 13.
28. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 14.
29. A Thin Film Inorganic Light Emitting Diode device comprising a coated layer containing ZnS:Cu particles prepared by a method according to claim 15.